



ON Semiconductor®

RHRG3060-F085 30A, 600V Hyperfast Rectifier

Max Ratings (600V, 30A)

The RHRG3060-F085 is an Hyperfast™ diode with soft recovery characteristics ($t_{rr} < 45\text{ns}$). It has half the recovery time of ultrafast diode and is of silicon nitride passivated ion-implanted epitaxial planar construction. This device is intended for use as a freewheeling/clamping diode and rectifier in a variety of automotive switching power supplies and other power switching automotive applications. Its low stored charge and hyperfast soft recovery minimize ringing and electrical noise in many power switching circuits, thus reducing power loss in the switching transistors.

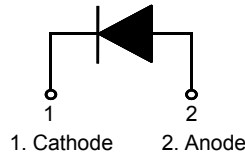
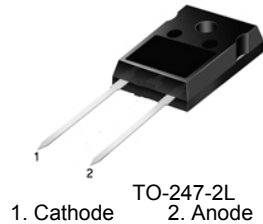
Features

- High Speed Switching ($t_{rr}=45\text{ns(Typ.)}$ @ $I_F=30\text{A}$)
- Low Forward Voltage ($V_F=1.64\text{V(Typ.)}$ @ $I_F=30\text{A}$)
- Avalanche Energy Rated
- AEC-Q101 Qualified

Applications

- Switching Power Supply
- Power Switching Circuits
- Automotive and General Purpose

Pin Assignments



Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Units
V_{RRM}	Peak Repetitive Reverse Voltage	600	V
V_{RWM}	Working Peak Reverse Voltage	600	V
V_R	DC Blocking Voltage	600	V
$I_{F(AV)}$	Average Rectified Forward Current @ $T_C = 25^\circ\text{C}$	30	A
I_{FSM}	Non-repetitive Peak Surge Current (Halfwave 1 Phase 50Hz)	90	A
E_{AVL}	Avalanche Energy (1A, 40mH)	20	mJ
T_J, T_{STG}	Operating Junction and Storage Temperature	- 55 to +175	$^\circ\text{C}$

Thermal Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Max	Units
$R_{\theta JC}$	Maximum Thermal Resistance, Junction to Case	0.66	$^\circ\text{C/W}$
$R_{\theta JA}$	Maximum Thermal Resistance, Junction to Ambient	45	$^\circ\text{C/W}$

Package Marking and Ordering Information

Device Marking	Device	Package	Tube	Quantity
RHRG3060	RHRG3060-F085	TO-247	-	30

RHRG3060-F085 30A, 600V Hyperfast Rectifier

Electrical Characteristics T_C = 25°C unless otherwise noted

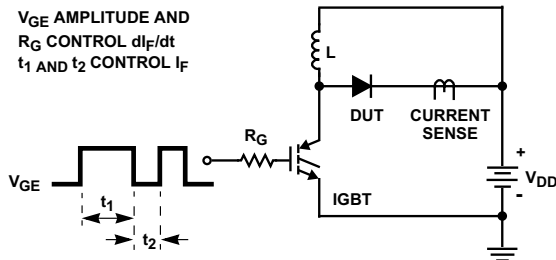
Symbol	Parameter	Conditions	Min.	Typ.	Max	Units	
I _R	Instantaneous Reverse Current	V _R = 600V	T _C = 25 °C	-	-	250	uA
			T _C = 175 °C	-	-	1.5	mA
V _{FM} ¹	Instantaneous Forward Voltage	I _F = 30A	T _C = 25 °C	-	1.64	2.1	V
			T _C = 175 °C	-	1.24	1.7	V
t _{rr} ²	Reverse Recovery Time	I _F = 1A, di/dt = 200A/μs, V _{CC} = 390V	T _C = 25 °C	-	24	40	ns
		I _F = 30A, di/dt = 200A/μs, V _{CC} = 390V	T _C = 25 °C	-	33	45	ns
			T _C = 175 °C	-	136	-	ns
t _a	Reverse Recovery Time	I _F = 30A, di/dt = 200A/μs, V _{CC} = 390V	T _C = 25 °C	-	19	-	ns
t _b			-	14	-	ns	
Q _{rr}	Reverse Recovery Charge		-	60	-	nC	

Notes:

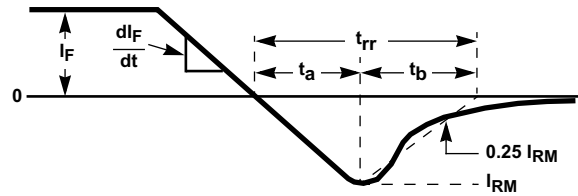
1. Pulse : Test Pulse width = 300μs, Duty Cycle = 2%
2. Guaranteed by design

Test Circuit and Waveforms

t_{rr} Test Circuit

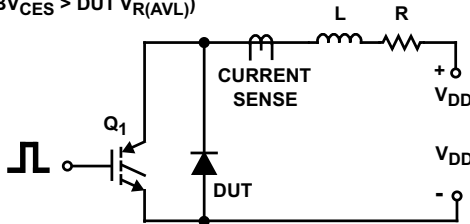


t_{rr} Waveforms and Definitions

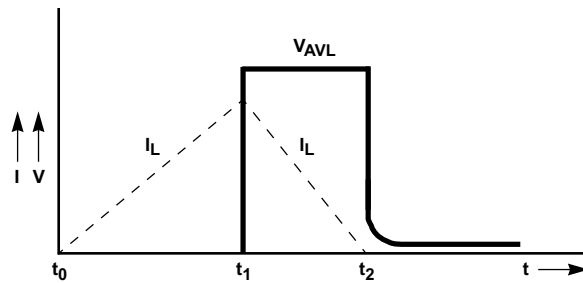


Avalanche Energy Test Circuit

I = 1A
L = 40mH
R < 0.1Ω
E_{AVL} = 1/2LI² [V_{R(AVL)}/(V_{R(AVL)} - V_{DD})]
Q₁ = IGBT (BV_{CES} > DUT V_{R(AVL)})



Avalanche Current and Voltage Waveforms



Typical Performance Characteristics

Figure 1. Typical Forward Voltage Drop vs. Forward Current

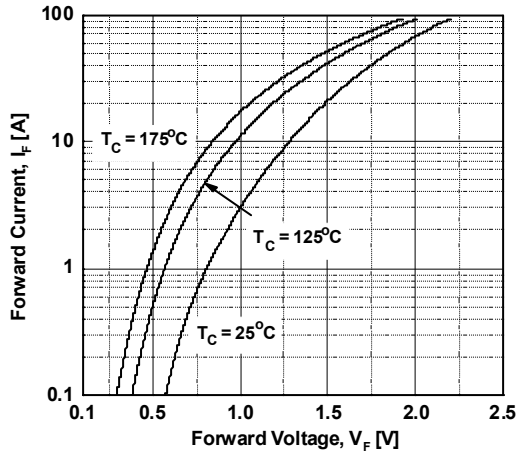


Figure 3. Typical Junction Capacitance

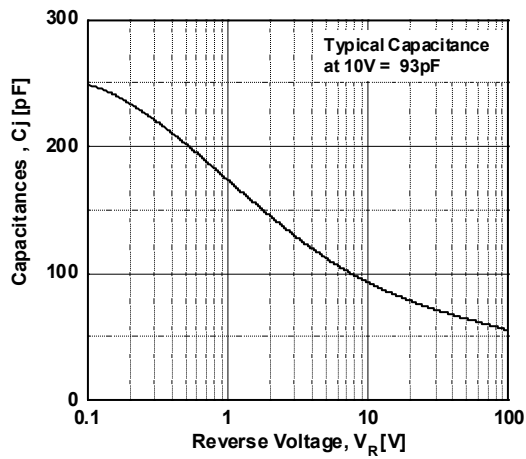


Figure 5. Typical Reverse Recovery Current vs. di/dt

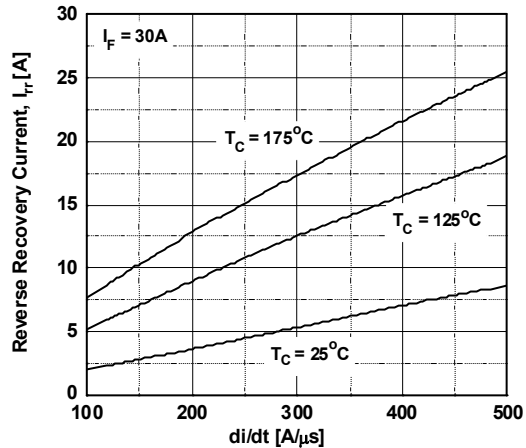


Figure 2. Typical Reverse Current vs. Reverse Voltage

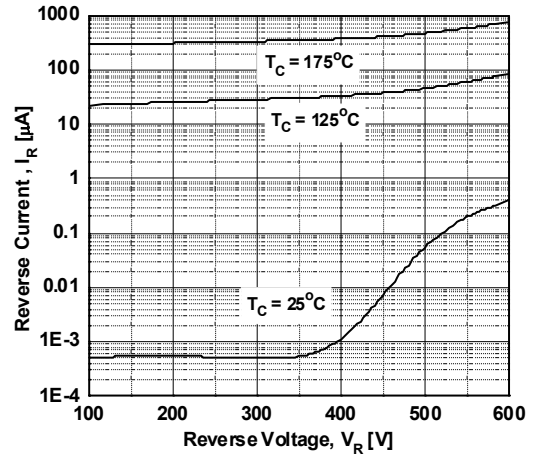


Figure 4. Typical Reverse Recovery Time vs. di/dt

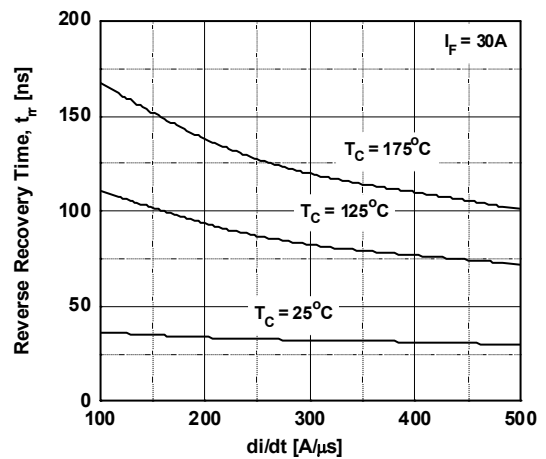
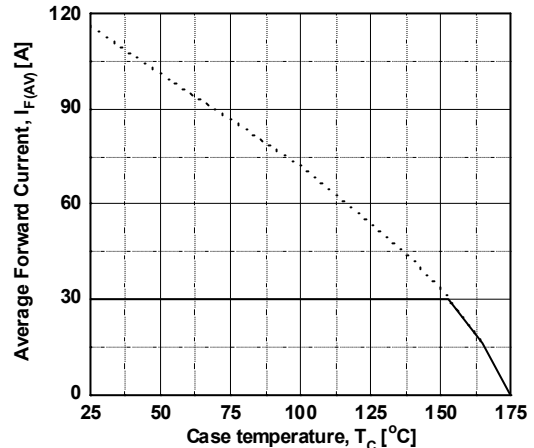


Figure 6. Forward Current Derating Curve



Typical Performance Characteristics (Continued)

Figure 7. Reverse Recovery Charge

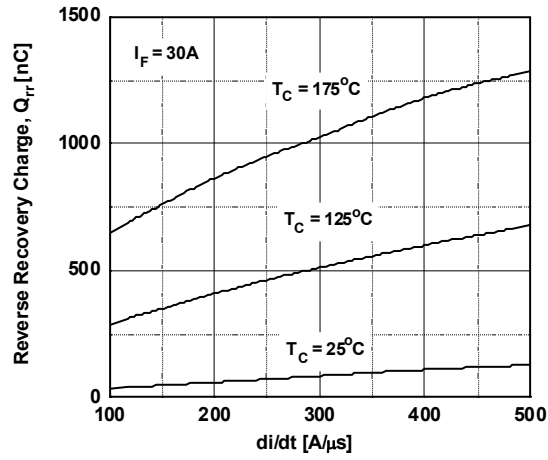
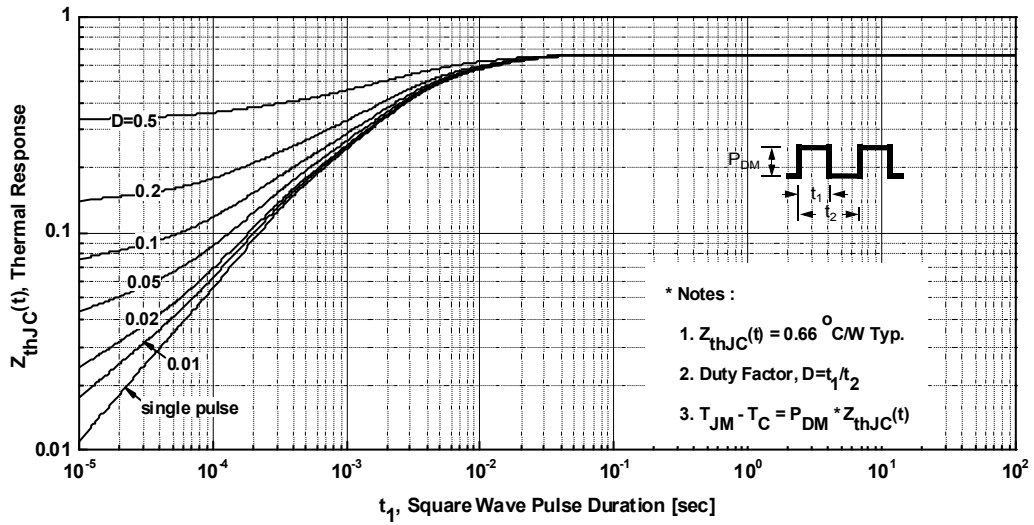
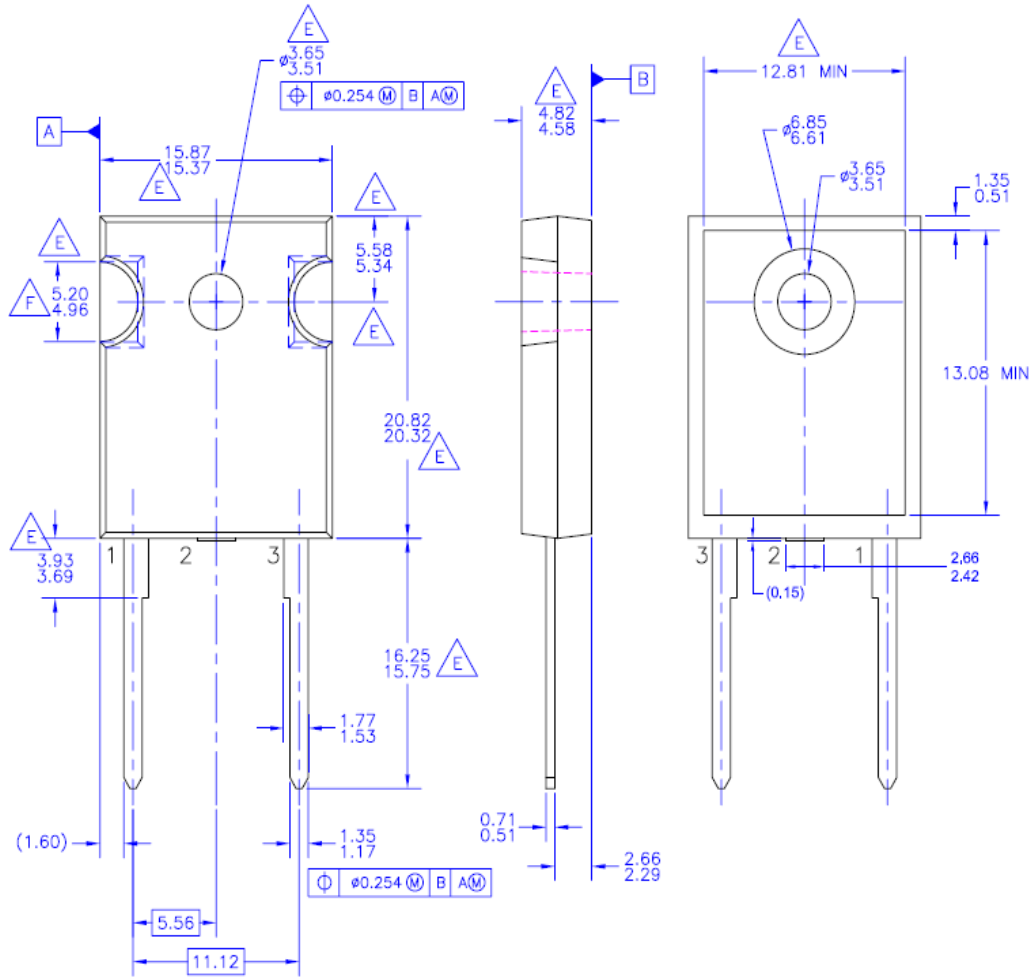


Figure 8. Transient Thermal Response Curve



Mechanical Dimensions

TO-247-2L



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Dimensions in Millimeters

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